

Title (en)

VERY HIGH CAPACITANCE FILM CAPACITOR AND METHOD FOR THE PRODUCTION OF SAME

Title (de)

SCHICHTKONDENSATOR MIT SEHR HOHER KAPAZITÄT UND VERFAHREN ZUR HERSTELLUNG DAVON

Title (fr)

CONDENSATEUR FILM A TRÈS HAUTE CAPACITÉ ET SON PROCÉDÉ DE FABRICATION

Publication

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Application

EP 17771785 A 20170928

Priority

- FR 1659489 A 20161003
- EP 2017074619 W 20170928

Abstract (en)

[origin: CA3036330A1] The present invention relates in particular to a very high capacitance film capacitor (1) that comprises a dielectric layer (100) consisting of at least one dielectric film (100a,..., 100i), each dielectric film (100a,..., 100i) of this dielectric layer (100) having the following parameters: - a relative dielectric permittivity [ef i] such that $ef\ i = 10$, - a thickness [ef i] such that $0.05\ \mu\text{m} = ef\ i = 50\ \mu\text{m}$, - a dielectric strength [Ef i] such that $Ef\ i = 50\ \text{V}/\mu\text{m}$, parameters in which "f" signifies "film" and i = 1, "i" designating the "ith" dielectric film (100i) of said dielectric layer (100), this dielectric layer (100) separating a first electronic charge carrier structure (200) from a second electronic charge carrier structure (300), these two structures having an opposite surface (S) separated by the dielectric layer(100).

IPC 8 full level

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Citation (search report)

See references of WO 2018065289A1

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